

Jiyuan Zheng

List of Publications by Year in descending order

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22
papers

243
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22
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citing authors

#	ARTICLE	IF	CITATIONS
1	Atomistic Transport Modeling, Design Principles, and Empirical Rules for Low-Noise III-V Digital-Alloy Avalanche Photodiodes. <i>Physical Review Applied</i> , 2022, 17, .	3.8	4
2	Dynamic-quenching of a single-photon avalanche photodetector using an adaptive resistive switch. <i>Nature Communications</i> , 2022, 13, 1517.	12.8	5
3	Biaxial strain modulated valence-band engineering in III-V digital alloys. <i>Physical Review B</i> , 2022, 106, .	3.2	0
4	A Physics Based Multiscale Compact Model of p-i-n Avalanche Photodiodes. <i>Journal of Lightwave Technology</i> , 2021, 39, 3591-3598.	4.6	4
5	A Comprehensive Modeling Approach of Electronic Properties in III-V Digital Alloys. , 2021, , .		0
6	Full band Monte Carlo simulation of AlInAsSb digital alloys. <i>Informa \AA Mater</i> , 2020, 2, 1236-1240.	17.3	8
7	Comparison of Different Period Digital Alloy $\text{Al}_{0.7}\text{InAsSb}$ Avalanche Photodiodes. <i>Journal of Lightwave Technology</i> , 2019, 37, 3647-3654.	4.6	11
8	Characterization of band offsets in $\text{Al}_x\text{In}_{1-x}\text{As}_y\text{Sb}_{1-y}$ alloys with varying Al composition. <i>Applied Physics Letters</i> , 2019, 115, .	3.3	17
9	AlInAsSb Impact Ionization Coefficients. <i>IEEE Photonics Technology Letters</i> , 2019, 31, 315-318.	2.5	25
10	Stark-Localization-Limited Franz-Keldysh Effect in InAlAs Digital Alloys. <i>Physica Status Solidi - Rapid Research Letters</i> , 2019, 13, 1900272.	2.4	2
11	Near ultraviolet enhanced 4H-SiC Schottky diode. <i>Applied Physics Letters</i> , 2019, 115, .	3.3	12
12	Understanding the Role of Minigaps in APDs: Towards Designing a Better Photodetector. , 2019, , .		0
13	APD Performance Enhancement: Minigap Engineering in Digital Alloys. , 2018, , .		2
14	Comparison of Excess Noise in InAlAs and AlGaAs Digital and Random Alloy Avalanche Photodiodes. , 2018, , .		0
15	Digital Alloy-Based Avalanche Photodiodes. , 2018, , .		2
16	Digital Alloy InAlAs Avalanche Photodiodes. <i>Journal of Lightwave Technology</i> , 2018, 36, 3580-3585.	4.6	35
17	Temperature dependence of the ionization coefficients of InAlAs and AlGaAs digital alloys. <i>Photonics Research</i> , 2018, 6, 794.	7.0	27
18	Theoretical study on interfacial impact ionization in AlN/GaN periodically stacked structure. <i>Applied Physics Express</i> , 2017, 10, 071002.	2.4	12

#	ARTICLE	IF	CITATIONS
19	The Influence of Structure Parameter on GaN/AlN Periodically Stacked Structure Avalanche Photodiode. IEEE Photonics Technology Letters, 2017, 29, 2187-2190.	2.5	11
20	A PMT-like high gain avalanche photodiode based on GaN/AlN periodically stacked structure. Applied Physics Letters, 2016, 109, .	3.3	45
21	Low-temperature-dependent property in an avalanche photodiode based on GaN/AlN periodically-stacked structure. Scientific Reports, 2016, 6, 35978.	3.3	11
22	Study on spin and optical polarization in a coupled InGaN/GaN quantum well and quantum dots structure. Scientific Reports, 2016, 6, 35597.	3.3	10